



Product Overview

BD810: High Power PNP Bipolar Transistor

For complete documentation, see the data sheet

Product Description

The High Power NPN Bipolar Power Transistor is designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.

Features

- DC Current Gain - $h_{FE} = 30$ (Min) @ $I_C = 2.0$ Adc
- Pb-Free Packages are Available

Part Electrical Specifications

Product	Compliance	Status	Polarity	I_C Continuous (A)	$V_{(BR)CEO}$ Min (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
BD810G	Pb-free	Active	PNP	10	80	30	-	1.5	90	TO-220-3

For more information please contact your local sales support at www.onsemi.com

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